2SB647(A)

Rev.E Mar.-2016

DATA SHEET

WR0<50P ṂṂ Ŀ SQS ᴁṀ ɥ s ǁ ᒣ Silicon PNP transistor in a TO-92LM Plastic Package.

љ 5VG99 : +D, Йˏ ´

Complementary pair with 2SD667(A).

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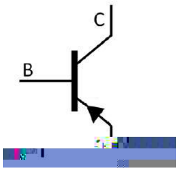
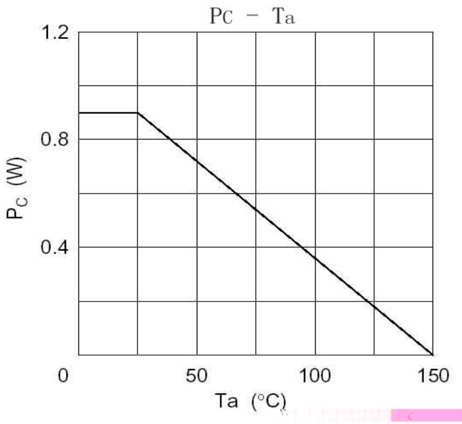
Low frequency power amplifier.

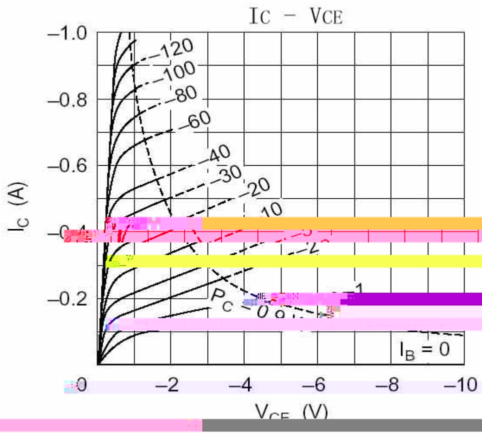


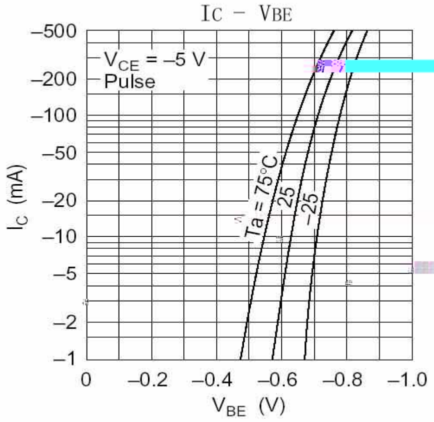
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

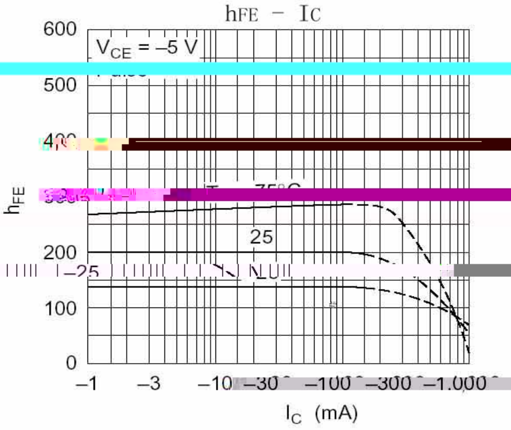
v ‟Ω Parameter	ɣ ᴺ Symbol		‟Ω Ө Rating	D ᵹ Unit
Collector to Base Voltage	V_{CBO}		-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647	-80	V
		2SB647A	-100	
Emitter to Base Voltage	V_{EBO}		-5.0	V
Collector Current (DC)	I_C		-1.0	A
Collector Current(Pulse)	I_{CP}		-2.0	A
Collector Power Dissipation	P_C		900	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T			

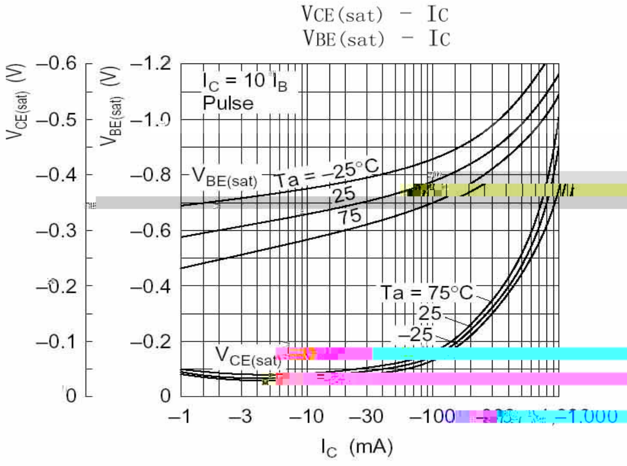
/ Electrical Characteristic Curve

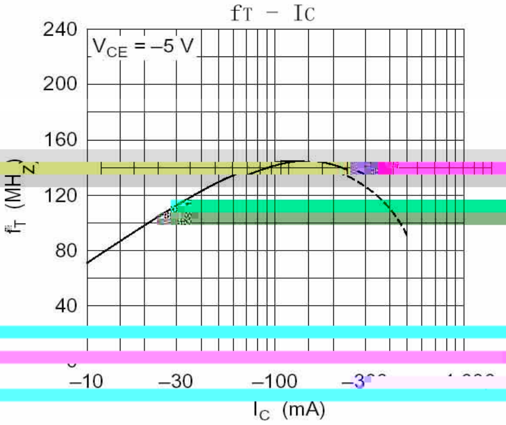

PC － Ta


IC － VCE


IC － VBE

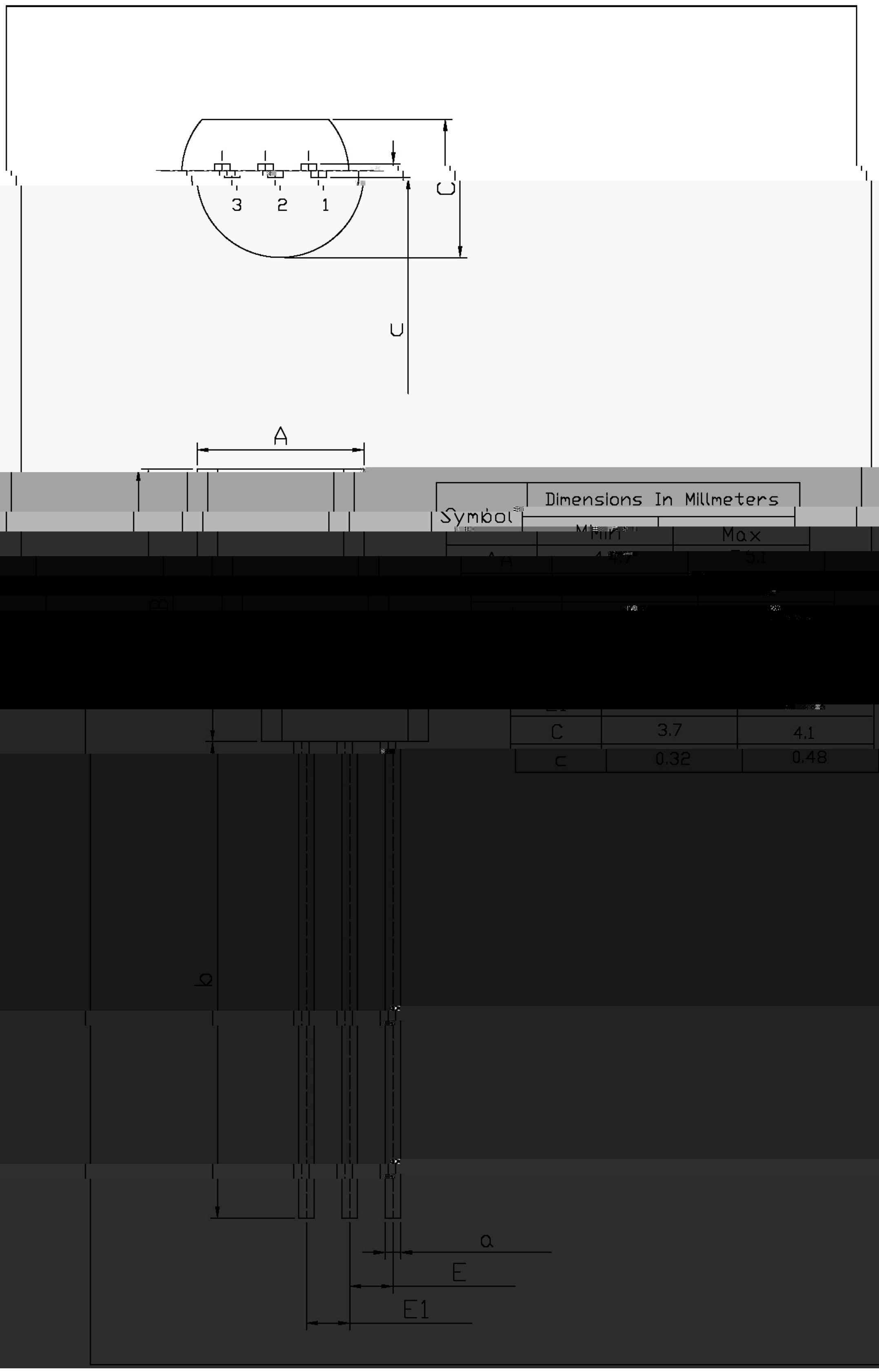

hFE － IC


VCE(sat) － IC
VBE(sat) － IC


fT － IC

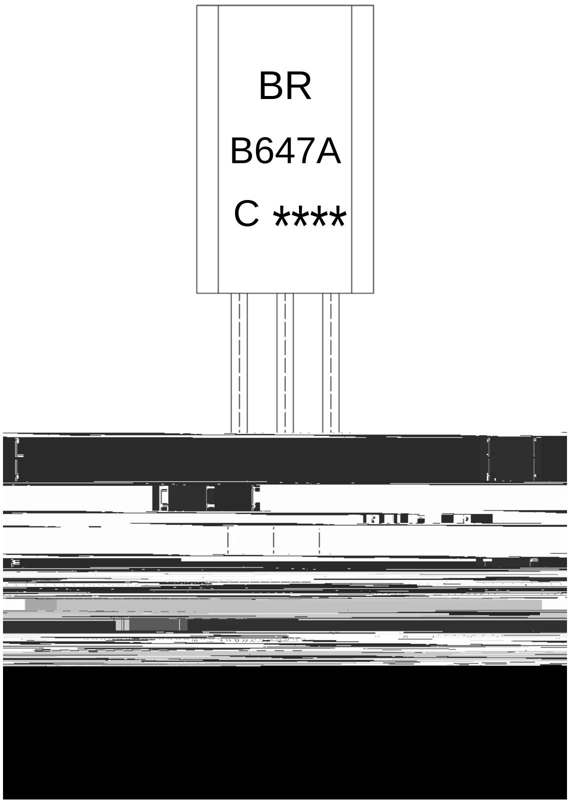
/ Package Dimensions

TO-92LM Unit: mm



Symbol	Dimensions In Millmeters	
	Min	Max
A	4.7	5.1
[illegible]	[illegible]	[illegible]
C	3.7	4.1
c	0.32	0.48

/ Marking Instructions



ب ˝ χ

EU:	㓺 ㄋ ᴻ ᒥᑐ
E97 : D χ	㓺 ʒ ᴺ ᒥᑐ
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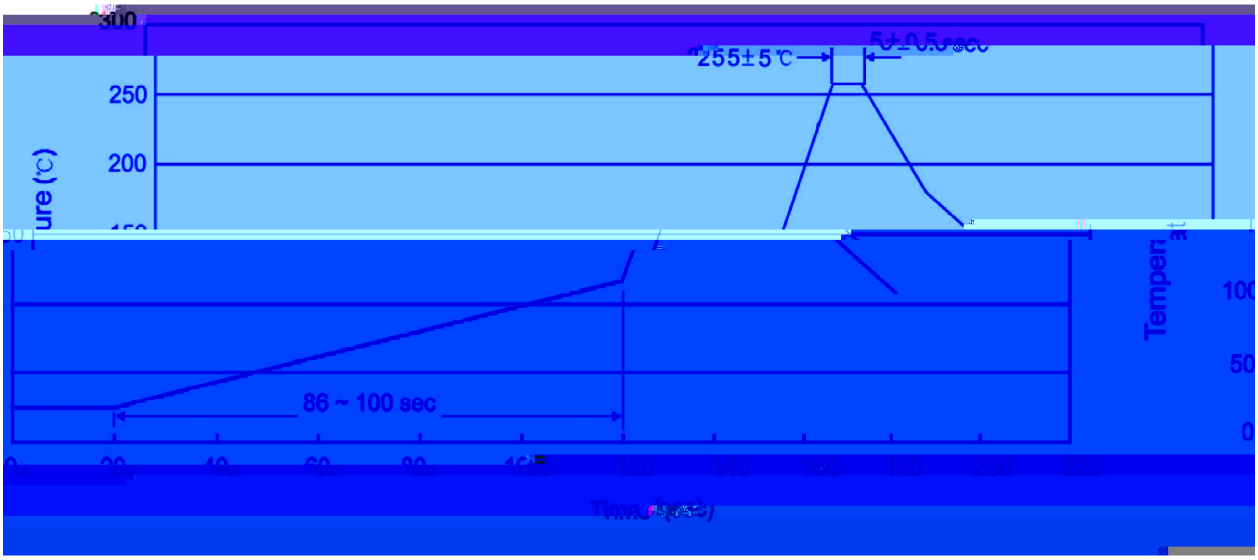
---- χ	㓺 ꞁ ғ ῆ ᴺ ᒥᑐ ꞁ ୫ ꞁ ғ ῆ ᴺ ψ ק

Note:

BR:	Company Code.
B647A:	Product Type.
C:	h_{FE} Classifications Symbol
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



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1 ỉ ♬ □ ẙ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;

Note:

1.Preheating:25~150 ɫ